

### Surface Mount N-Channel MOSFET

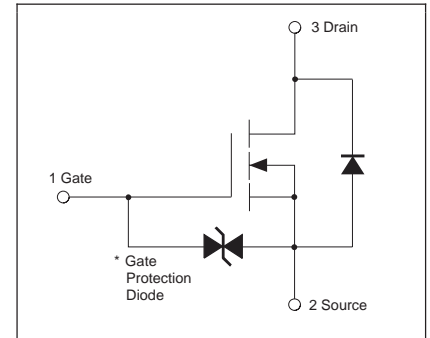
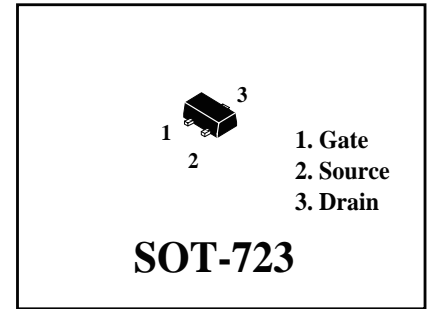
**(Pb)** Lead(Pb)-Free

#### Features:

- \* Low on-resistance
- \* Fast switching speed
- \* Low voltage drive(2.5V) makes this ideal for portable equipment
- \* Drive Circuits Are Simple
- \* Parallel Use is Easy
- \* Yieldable What the Material of Product
- \* Compliance with RoHS Requirements.

#### Applications:

- \* Interfacing, switching(30V, 100mA)



### Maximum Ratings( $T_A=25^\circ\text{C}$ Unless Otherwise Specified)

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	
Continuous Drain Current	$I_D$	$\pm 100$	mA
Power Dissipation	$P_D$	150	mW
Pulsed Drain Current	$I_{DM}$	$\pm 400$	mA
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

\* Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1.  $P_w \leq 10\mu\text{s}$ , Duty Cycle  $\leq 1\%$
2. With Each Pin Mounted On The Recommended Lands.

## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Static</b>					
Drain-Source Breakdown Voltage @ $V_{GS}=0, I_D=10\mu\text{A}$	$V_{(BR)DSS}$	30	-	-	V
Gate Threshold Voltage @ $V_{DS}=3V, I_D=100\mu\text{A}$	$V_{GS(Th)}$	0.8	-	1.5	
Gate-Source Leakage current @ $V_{GS}=\pm 20V, V_{DS}=0V$	$I_{GSS}$	-	-	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current @ $V_{DS}=30V, V_{GS}=0$	$I_{DSS}$	-	-	1.0	$\mu\text{A}$
Drain-Source On-State Resistance @ $V_{GS}=4V, I_D=10\text{mA}$ @ $V_{GS}=2.5V, I_D=1\text{mA}$	$R_{DS(on)}$	-	5	8	$\Omega$
		-	7	13	
Forward Transfer Admittance @ $V_{DS}=3V, I_D=10\text{mA}$	$ Y_{fs} $	2.0	-	-	mS

## Dynamic

Input Capacitance @ $V_{GS}=0V, V_{DS}=5V, f=1.0\text{MHz}$	$C_{iss}$	-	13	-	pF
Output Capacitance @ $V_{GS}=0V, V_{DS}=5V, f=1.0\text{MHz}$	$C_{oss}$	-	9.0	-	
Reverse Transfer Capacitance @ $V_{GS}=0V, V_{DS}=5V, f=1.0\text{MHz}$	$C_{rss}$	-	4.0	-	

## Switching

Turn-on Delay Time $V_{GS}=5V, V_{DD}=5V, I_D=10\text{mA}, R_G=10\Omega, R_L=500\Omega$	$t_{d(on)}$	-	15	-	ns
Turn-on Rise Time $V_{GS}=5V, V_{DD}=5V, I_D=10\text{mA}, R_G=10\Omega, R_L=500\Omega$	$t_r$	-	35	-	
Turn-off Delay Time $V_{GS}=5V, V_{DD}=5V, I_D=10\text{mA}, R_G=10\Omega, R_L=500\Omega$	$t_{d(off)}$	-	80	-	
Turn-off Fall Time $V_{GS}=5V, V_{DD}=5V, I_D=10\text{mA}, R_G=10\Omega, R_L=500\Omega$	$t_f$	-	80	-	

## Device Marking

2SK3541M = KN

## Electrical Characteristic

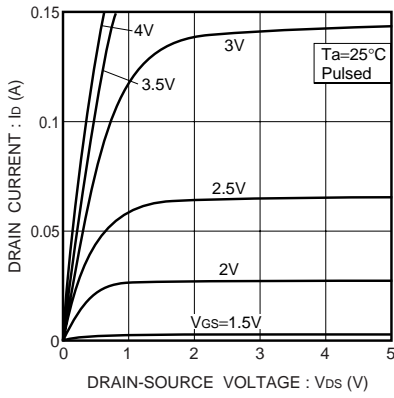


Fig.1 Typical output characteristics

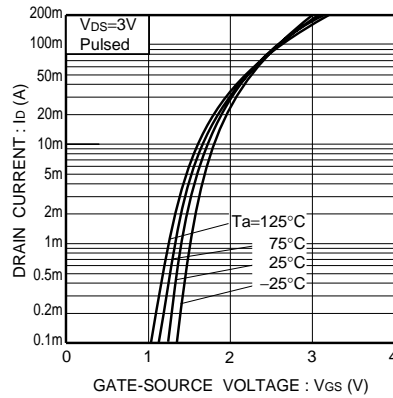


Fig.2 Typical transfer characteristics

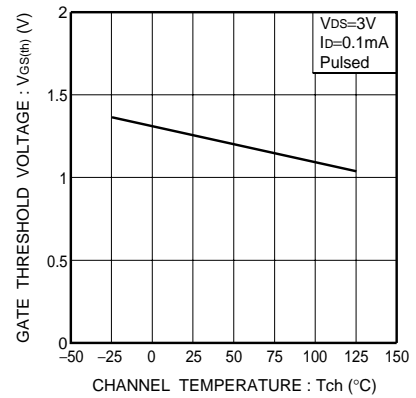


Fig.3 Gate threshold voltage vs. channel temperature

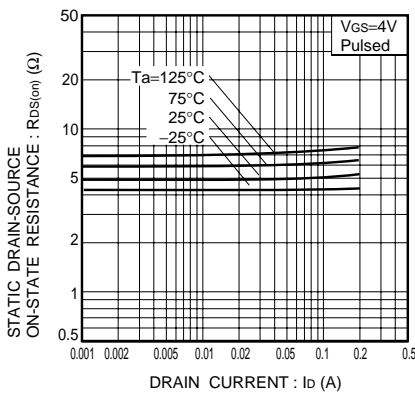


Fig.4 Static drain-source on-state resistance vs. drain current (I)

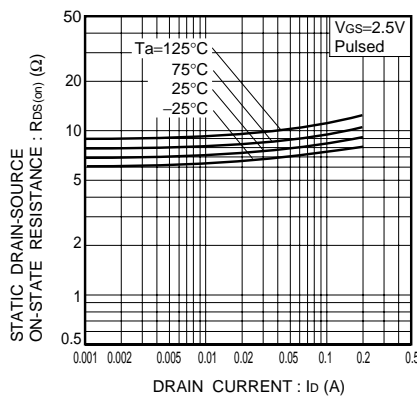


Fig.5 Static drain-source on-state resistance vs. drain current (II)

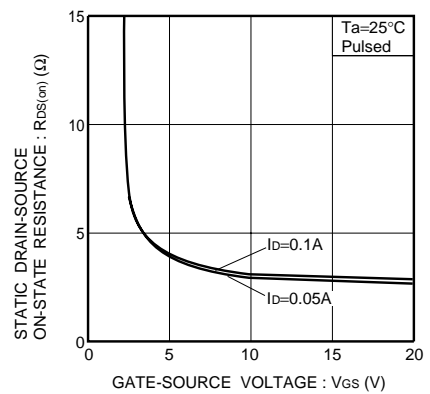


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

## Typical Characteristics

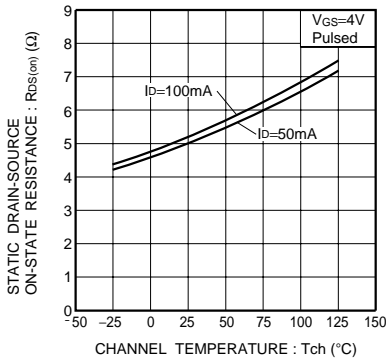


Fig.7 Static drain-source on-state resistance vs. channel temperature

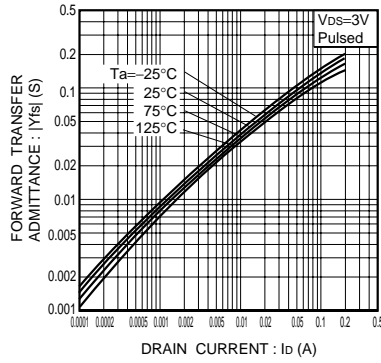


Fig.8 Forward transfer admittance vs. drain current

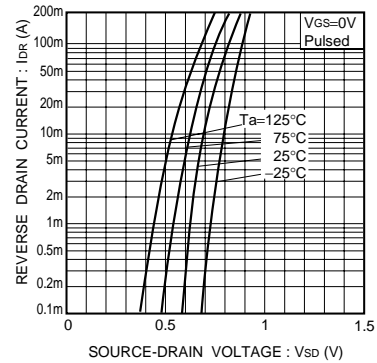


Fig.9 Reverse drain current vs. source-drain voltage (I)

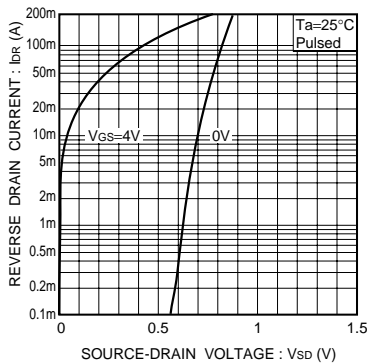


Fig.10 Reverse drain current vs. source-drain voltage (II)

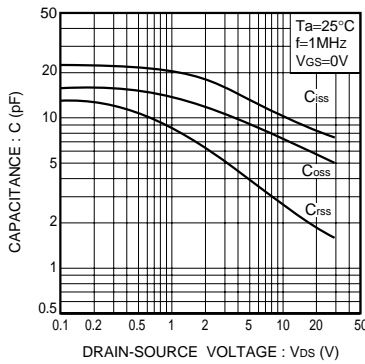


Fig.11 Typical capacitance vs. drain-source voltage

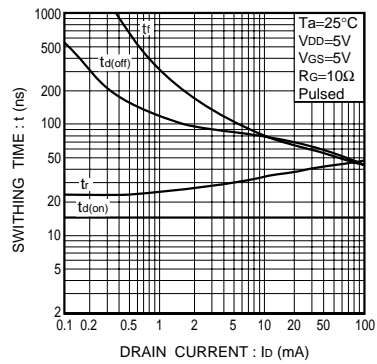


Fig.12 Switching characteristics (See Figures 13 and 14 for the measurement circuit and resultant waveforms)

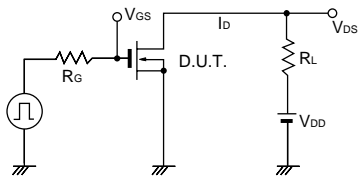


Fig.13 Switching time measurement circuit

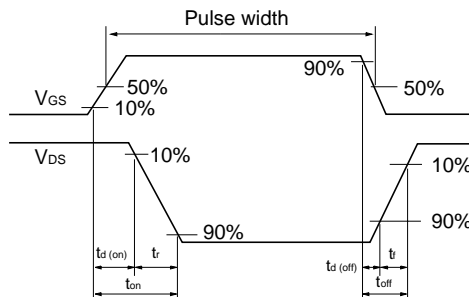
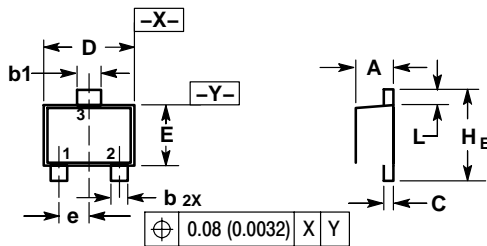


Fig.14 Switching time waveforms

## Typical Characteristics

### SOT-723

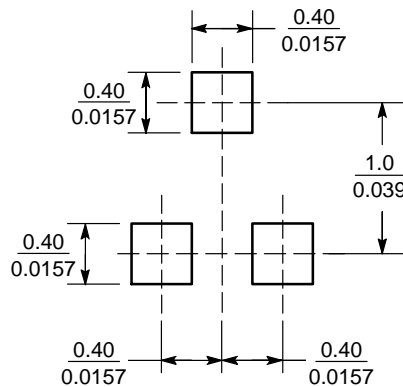


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.20	0.27	0.0059	0.0079	0.0106
b1	0.25	0.3	0.35	0.010	0.012	0.014
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H <sub>E</sub>	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

### SOLDERING FOOTPRINT



( $\frac{\text{mm}}{\text{inches}}$ )